

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A process of reforming a quartz glass crucible, wherein the quartz glass crucible is reformed by an arc discharge generated by electrodes positioned around a rotational axis and configured to heat an inside surface of the crucible while the crucible is rotated, the process comprising:

~~arranging the electrodes in~~ using an electrode structure in which having 3n electrodes with 3-phase alternating electric current, n being equal to or larger than 2, wherein  
neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration[[;]] ~~determining a phase of an electric current based on a number and an arrangement of the electrodes; forming~~ so as to form a stable ring-like arc between the neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration, ~~by applying electric current of the determined phase to the electrodes;~~

heating the inside surface of the crucible while the crucible is rotated; and

removing one of a foreign substance located on the inside surface and a bubble located under the inside surface.

2. (Currently Amended) The process of claim 1, wherein the ~~arranging~~ using step comprises:

arranging the electrodes in the electrode structure such that the neighboring electrodes are positioned at regular intervals in the ring-like configuration so as to have an absolute value  $\theta$  of a phase difference of the alternating electric current in the range of  $90^\circ \leq \theta \leq 180^\circ$ .

3. (Original) The process of claim 1, wherein a radius  $r$  of the ring-like configuration around the rotational axis is at least  $\frac{1}{4}$  of a radius  $R$  of an open portion of the crucible, for at least a fixed time during arc heating.

4. (Original) The process of claim 1, wherein a diameter of the crucible is 28 to 40 inches.

5. (Original) The process of claim 1, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

6. (Original) The process of claim 2, wherein a diameter of the crucible is 28 to 40 inches.

7. (Original) The process of claim 2, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

8. (Original) The process of claim 2, wherein a radius  $r$  of the ring-like configuration around the rotational axis is at least  $\frac{1}{4}$  of a radius  $R$  of an open portion of the crucible, for at least a fixed time during arc heating.

9. (Original) The process of claim 8, wherein a diameter of the crucible is 28 to 40 inches.

10. (Original) The process of claim 8, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

11. (Original) The process of claim 3, wherein a diameter of the crucible is 28 to 40 inches.

12. (Original) The process of claim 3, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

13. (Currently Amended) A process of reforming a quartz glass crucible, comprising:

one of mechanically removing a foreign substance on an inside surface of the crucible and removing a bubble just under the inside surface of the crucible by grinding;

~~arranging electrodes in using~~ an electrode structure ~~such that~~ having  $3n$  electrodes with 3-phase alternating electric current,  $n$  being equal to or larger than 2, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration[[:]] ~~determining a phase of an electric current based on a number and an arrangement of the electrodes;~~ so as to form ~~forming~~ a ring-like arc between neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration, ~~by applying electric current of the determined phase to the electrodes;~~ and

fusing the inside surface of the crucible to be smoothed.

14. (Original) The process of claim 13, wherein a diameter of the crucible is 28 to 40 inches.

15. (Previously Presented) The process of claim 13, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

16-17. (Canceled)

18. (New) A process of reforming a quartz glass crucible, wherein the quartz glass crucible is reformed by an arc discharge generated by electrodes positioned around a rotational axis and configured to heat an inside surface of the crucible while the crucible is rotated, the process comprising:

using an electrode structure having  $2n$  electrodes with 2-phase alternating electric current,  $n$  being equal to or larger than 2, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration so as to form a stable ring-like arc between the neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration;

heating the inside surface of the crucible while the crucible is rotated; and

removing one of a foreign substance located on the inside surface and a bubble located under the inside surface.

19. (New) A process of reforming a quartz glass crucible, wherein the quartz glass crucible is reformed by an arc discharge generated by electrodes positioned around a rotational axis and configured to heat an inside surface of the crucible while the crucible is rotated, the process comprising:

using an electrode structure having 8 electrodes with 4-phase alternating electric current, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration so as to form a stable ring-like arc between the neighboring

electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration;

heating the inside surface of the crucible while the crucible is rotated; and

removing one of a foreign substance located on the inside surface and a bubble located under the inside surface.